



# STU7NB90 STU7NB90I

## N-CHANNEL 900V - 1.1 $\Omega$ - 7.3 A Max220/Max220I PowerMesh™ MOSFET

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STU7NB90	900 V	< 1.45 $\Omega$	7.3 A
STU7NB90I	900 V	< 1.45 $\Omega$	7.3 A

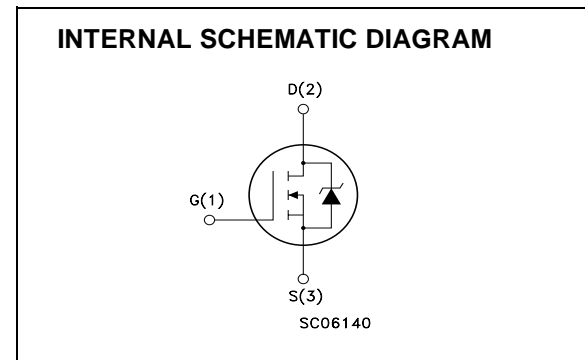
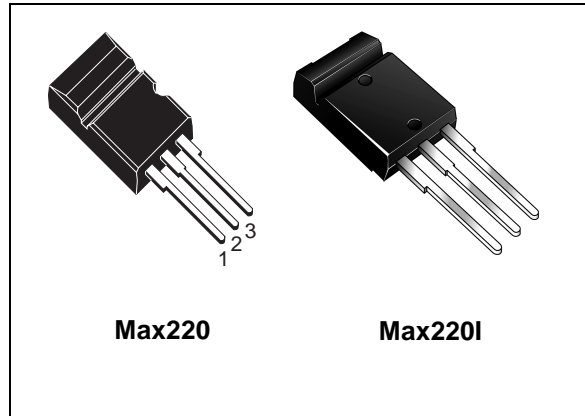
- TYPICAL R<sub>DS(on)</sub> = 1.1  $\Omega$
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- VERY LOW INTRINSIC CAPACITANCES
- GATE CHARGE MINIMIZED
- REDUCED VOLTAGE SPREAD

### DESCRIPTION

Using the latest high voltage MESH OVERLAY™ process, STMicroelectronics has designed an advanced family of power MOSFETs with outstanding performances. The new patent pending strip layout coupled with the Company's proprietary edge termination structure, gives the lowest R<sub>DS(on)</sub> per area, exceptional avalanche and dv/dt capabilities and unrivalled gate charge and switching characteristics.

### APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- DC-AC CONVERTERS FOR WELDING EQUIPMENT



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STU7NB90	STU7NB90I	
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	900		V
V <sub>DGR</sub>	Drain-gate Voltage (R <sub>GS</sub> = 20 k $\Omega$ )	900		V
V <sub>GS</sub>	Gate- source Voltage	±30		V
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 25°C	7.3	7.3 (*)	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 100°C	4.6	4.6 (*)	A
I <sub>DM</sub> (●)	Drain Current (pulsed)	29.2	29.2 (*)	A
P <sub>TOT</sub>	Total Dissipation at T <sub>C</sub> = 25°C	170	60	W
	Derating Factor	1.36	0.47	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	4		V/ns
V <sub>ISO</sub>	Insulation Withstand Voltage (DC)	-	2500	V
T <sub>stg</sub>	Storage Temperature	-65 to 150		°C
T <sub>j</sub>	Max. Operating Junction Temperature	150		°C

(●) Pulse width limited by safe operating area

(1) I<sub>SD</sub> ≤ 7.3 A, di/dt ≤ 200A/μs, V<sub>DD</sub> ≤ V(BR)DSS, T<sub>j</sub> ≤ T<sub>JMAX</sub>.

(\*) Current Limited by Package

## STU7NB90 - STU7NB90I

### THERMAL DATA

		Max220	Max220I	
Rthj-case	Thermal Resistance Junction-case Max	0.734	2.1	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	62.5		°C/W
T <sub>l</sub>	Maximum Lead Temperature For Soldering Purpose	300		°C

### AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I <sub>AR</sub>	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T <sub>j</sub> max)	7.3	A
E <sub>AS</sub>	Single Pulse Avalanche Energy (starting T <sub>j</sub> = 25 °C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 50 V)	600	mJ

### ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED)

#### OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0	900			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating, T <sub>C</sub> = 125 °C			1 50	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ±30V			±100	nA

#### ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2	3	4	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 4 A		1.1	1.45	Ω

### DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (1)	Forward Transconductance	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>DS(on)max</sub> , I <sub>D</sub> = 4 A		8		S
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25V, f = 1 MHz, V <sub>GS</sub> = 0		2120		pF
C <sub>oss</sub>	Output Capacitance			225		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			23		pF

**ELECTRICAL CHARACTERISTICS (CONTINUED)**

**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 450\text{ V}, I_D = 3.5\text{ A}$ $R_G = 4.7\Omega, V_{GS} = 10\text{ V}$ (see test circuit, Figure 3)		25		ns
$t_r$	Rise Time			12		ns
$Q_g$	Total Gate Charge	$V_{DD} = 720\text{ V}, I_D = 7.4\text{ A},$ $V_{GS} = 10\text{ V}$		51	72	nC
$Q_{gs}$	Gate-Source Charge			12.5		nC
$Q_{gd}$	Gate-Drain Charge			23.5		nC

**SWITCHING OFF**

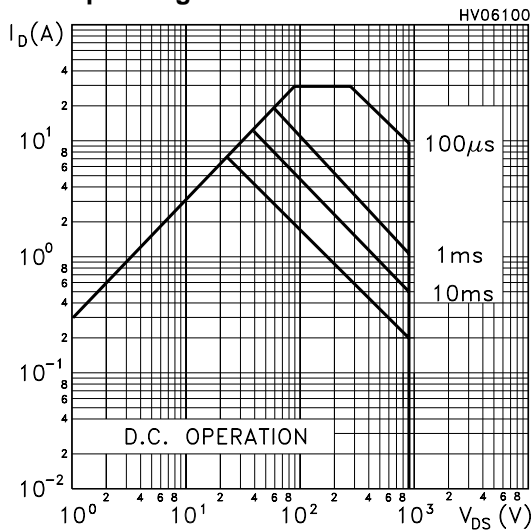
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 720\text{ V}, I_D = 7.4\text{ A},$ $R_G = 4.7\Omega, V_{GS} = 10\text{ V}$ (see test circuit, Figure 5)		22		ns
$t_f$	Fall Time			15		ns
$t_c$	Cross-over Time			31		ns

**SOURCE DRAIN DIODE**

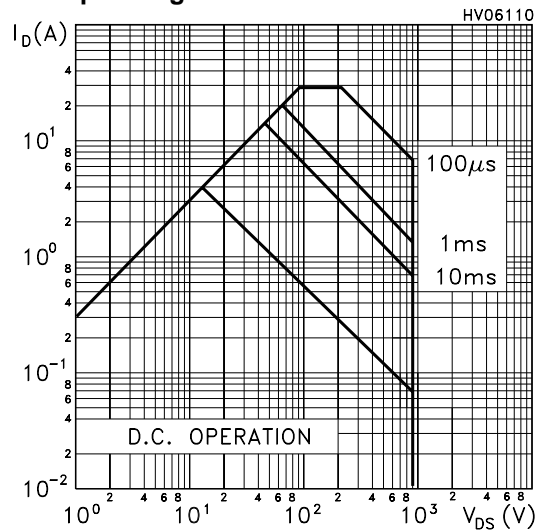
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain Current				7.3	A
$I_{SDM(2)}$	Source-drain Current (pulsed)				29.2	A
$V_{SD(1)}$	Forward On Voltage	$I_{SD} = 7.3\text{ A}, V_{GS} = 0$			1.6	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 7.4\text{ A}, di/dt = 100\text{ A}/\mu\text{s},$ $V_{DD} = 100\text{ V}, T_j = 150^\circ\text{C}$ (see test circuit, Figure 5)		700		ns
$Q_{rr}$	Reverse Recovery Charge			6.3		$\mu\text{C}$
$I_{RRM}$	Reverse Recovery Current			18		A

Note: 1. Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %.  
2. Pulse width limited by safe operating area.

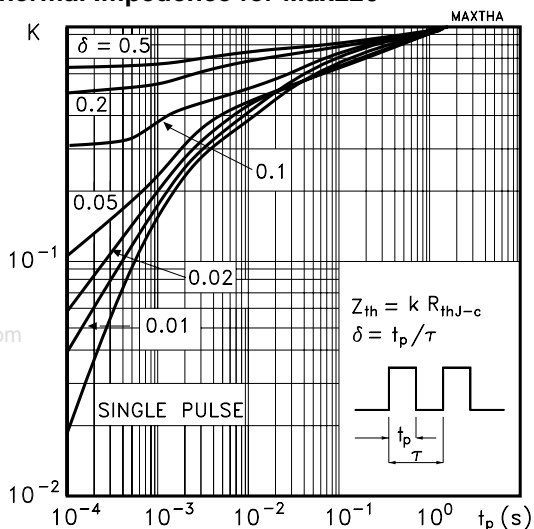
**Safe Operating Area for Max220**



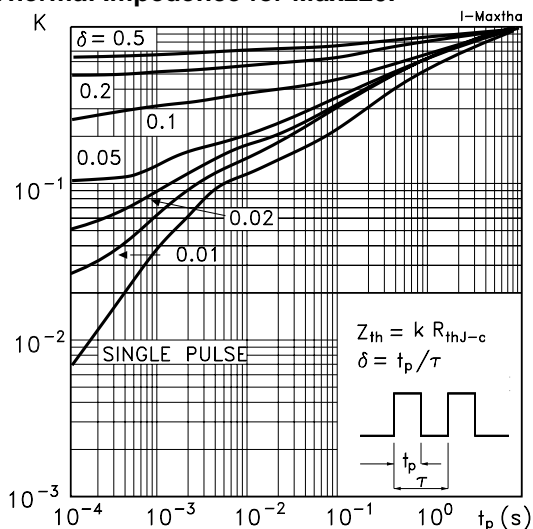
**Safe Operating Area for Max220I**



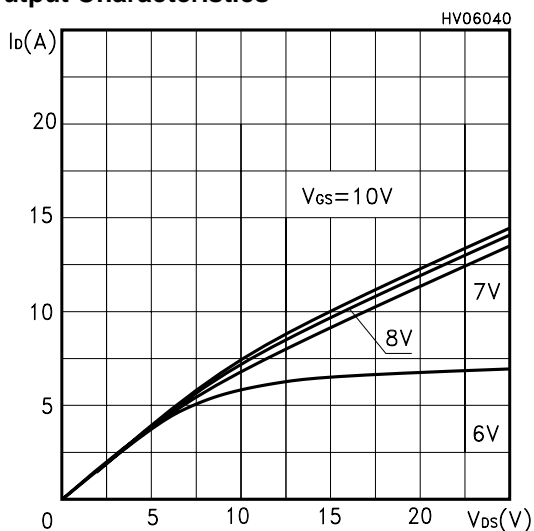
Thermal Impedance for Max220



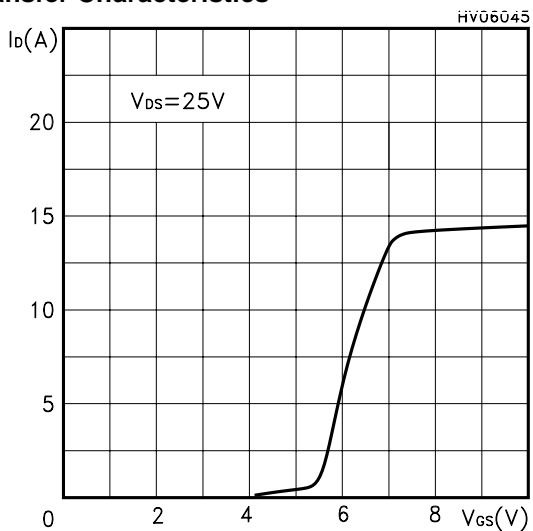
Thermal Impedance for Max220I



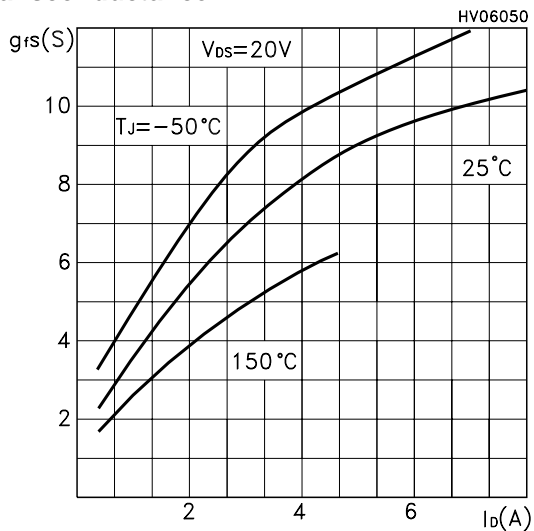
Output Characteristics



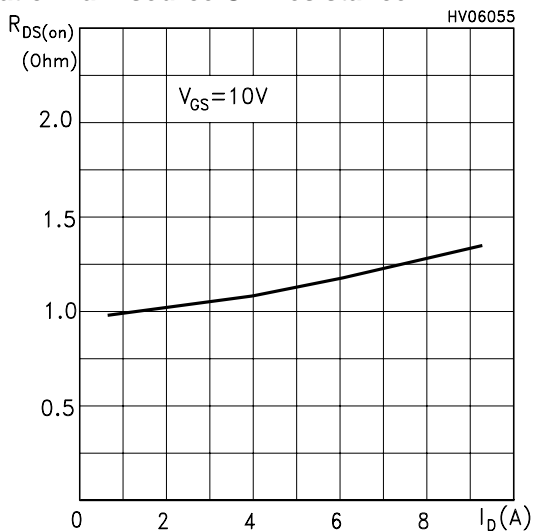
Transfer Characteristics



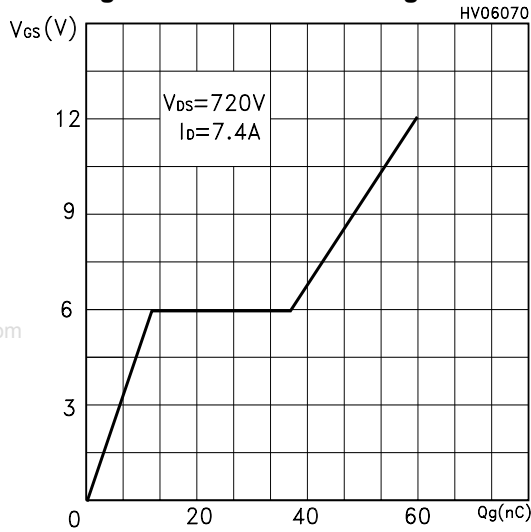
Transconductance



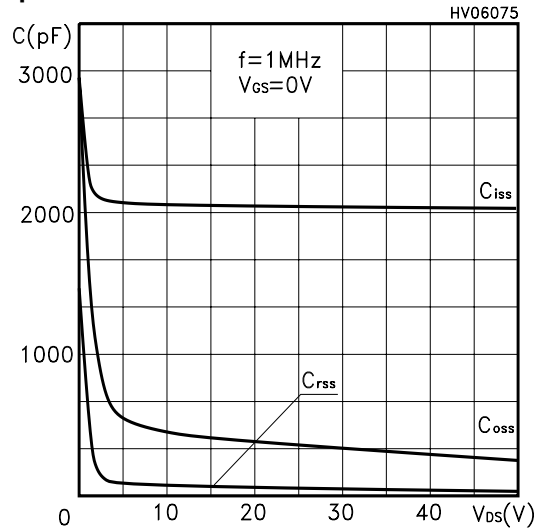
Static Drain-source On Resistance



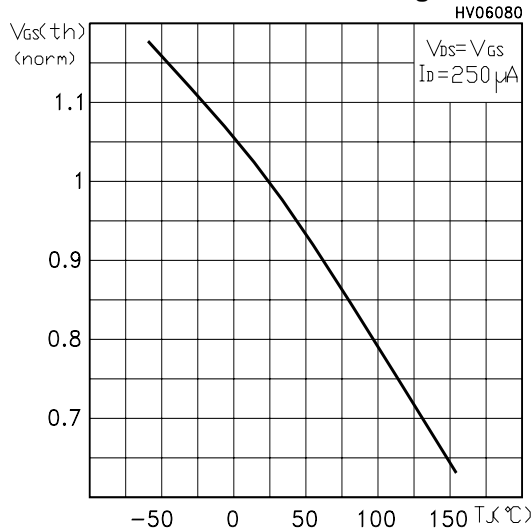
Gate Charge vs Gate-source Voltage



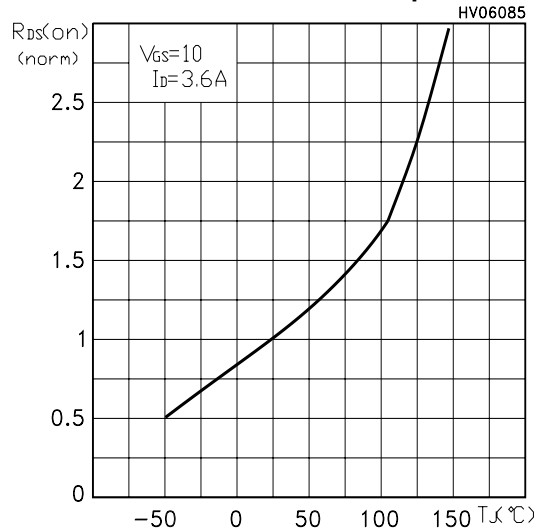
Capacitance Variations



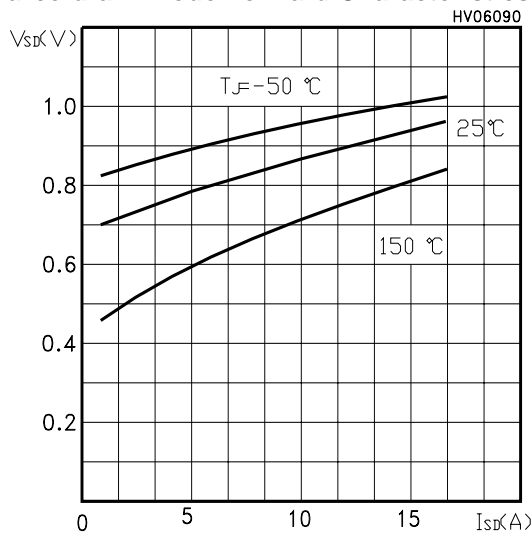
Normalized Gate Threshold Voltage vs Temp.



Normalized On Resistance vs Temperature

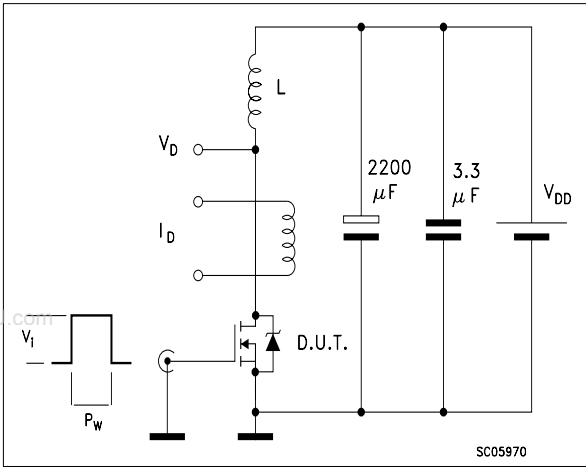


Source-drain Diode Forward Characteristics

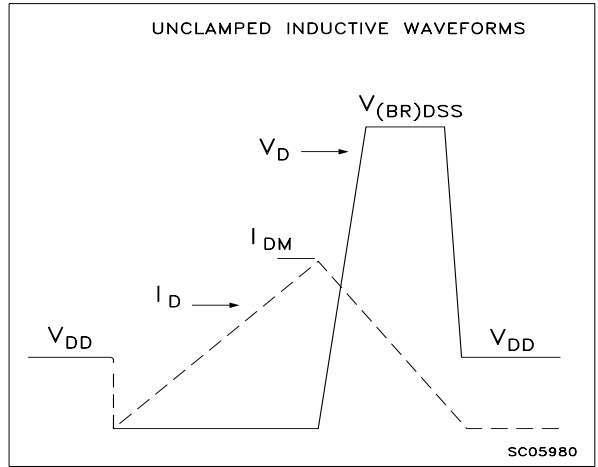


**STU7NB90 - STU7NB90I**

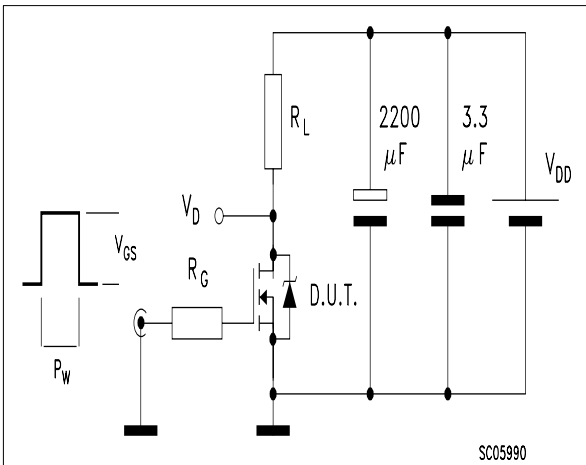
**Fig. 1: Unclamped Inductive Load Test Circuit**



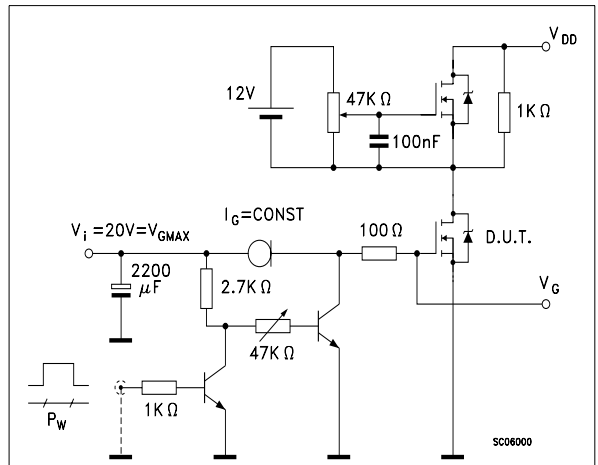
**Fig. 2: Unclamped Inductive Waveform**



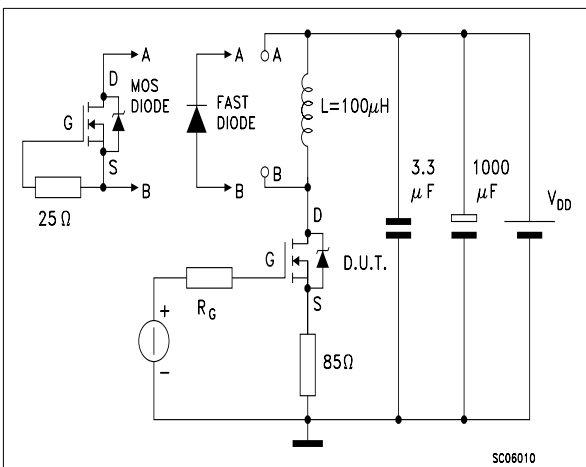
**Fig. 3: Switching Times Test Circuit For Resistive Load**



**Fig. 4: Gate Charge test Circuit**

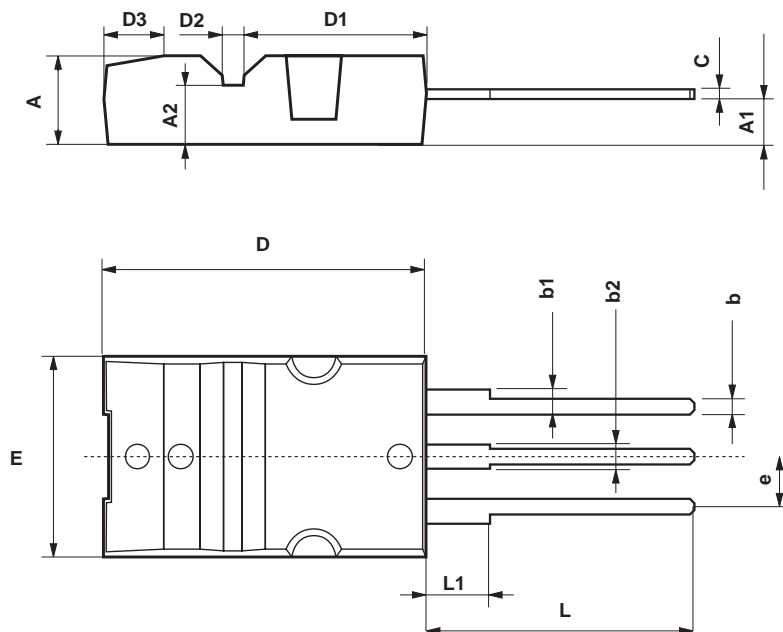


**Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times**



Max220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.3		4.6	0.169		0.181
A1	2.2		2.4	0.087		0.094
A2	2.9		3.1	0.114		0.122
b	0.7		0.93	0.027		0.036
b1	1.25		1.4	0.049		0.055
b2	1.2		1.38	0.047		0.054
c	0.45		0.6		0.18	0.023
D	15.9		16.3		0.626	0.641
D1	9		9.35	0.354		0.368
D2	0.8		1.2	0.031		0.047
D3	2.8		3.2	0.110		0.126
e	2.44		2.64	0.096		0.104
E	10.05		10.35	0.396		0.407
L	13.2		13.6	0.520		0.535
L1	3		3.4	0.118		0.133

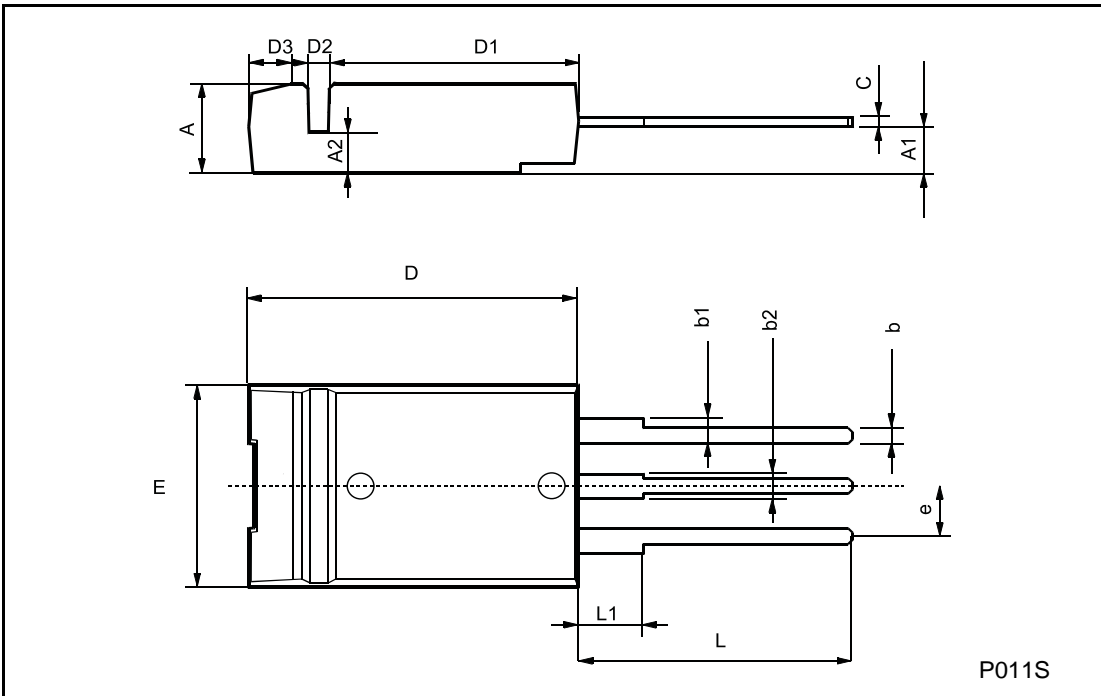


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I-Max220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.3		4.6	0.169		0.181
A1	2.6		2.75	0.102		0.108
A2	1.95		2.15	0.077		0.084
b	0.7		0.93	0.027		0.036
b1	1.25		1.4	0.049		0.055
b2	1.2		1.38	0.047		0.054
c	0.45		0.6	0.017		0.023
D	15.9		16.3	0.626		0.641
D1	12.5		12.9	0.492		0.508
D2	0.6		1	0.023		0.039
D3	1.75		2.15	0.069		0.084
e	2.44		2.64	0.096		0.104
E	10.05		10.35	0.396		0.407
L	13.2		13.6	0.520		0.535
L1	3		3.4	0.118		0.133

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